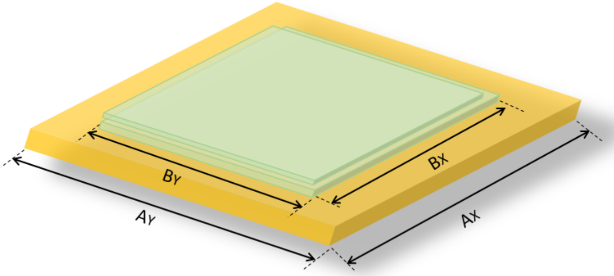
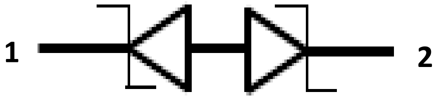
FB-3V3S33

Chip Bi - directional TVS diode





Mechanical Data	Notes
Dice size	AX:380um,AY:380um
Wafer size	4” (Gross die:40,320pcs/Good die>38,304pcs)
Chip Thickness	138um±12um
Scribe line width	60um
Top metal	Al/Au/Ag
Back side metal	Al/Au/Ag/Sn

Parameter	Symbol	Conditions	Value	Unit
Reverse stand-off voltage	V_{RWM}		3.3	V
Peak pulse power	P_{PP}	Tp=8/20us	250*	W
Peak pulse current	I_{PP}	Tp=8/20us	15.0*	A
Electrostatic discharge	V_{ESD}	IEC61000-4-2 Level-4	± 10(Contact) ±25(Air)	KV
Max.junction temp.	Tj		150	°C

Characteristics TA=25°C

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Breakdown voltage	V_{BR}	I_T=1mA	3.5			V
Reverse leakage current	I_R	V=±3.0V		0.05	0.9	uA
Snap-Back Voltage	Vsb	Isb=50mA	3.3		5.3	V
Clamping Voltage	V_C	I_{PP}=1.0A I_{PP}=15.0A			5.5* 10.0*	V
Diode capacitance	Cj	V_R=0V f=1MHz		25.0		pf

Notes:
(1)sampling testing:no bad dice inking/guaranteed good die >95%
(2)Testing follow customer
(3)Tj=Ta+Rth(j-a)*(pf+pr),where Rth(j-a)-thermal resistance,Pf-forward power dissipation,
Pr-revers power dissipation
(4)**For device testing